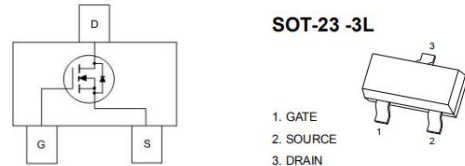


FS3404

SOT-23-3L 場效應晶體管(SOT-23-3L Field Effect Transistors)



N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

■ MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	30	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 20	V
Drain Current (continuous) 漏極電流-連續	I_D	5.8	A
Drain Current (pulsed) 漏極電流-脈沖	I_{DM}	20	A
Total Device Dissipation 總耗散功率 $T_A=25^{\circ}C$ 環境溫度為 $25^{\circ}C$	P_D	1500	mW
Junction 結溫	T_J	150	$^{\circ}C$
Storage Temperature 儲存溫度	T_{stg}	-55to+150	$^{\circ}C$

■ DEVICE MARKING 打標

FS3404=A4LA



FS3404

■ ELECTRICAL CHARACTERISTICS 電特性

(T_A=25°C unless otherwise noted 如無特殊說明, 溫度為 25°C)

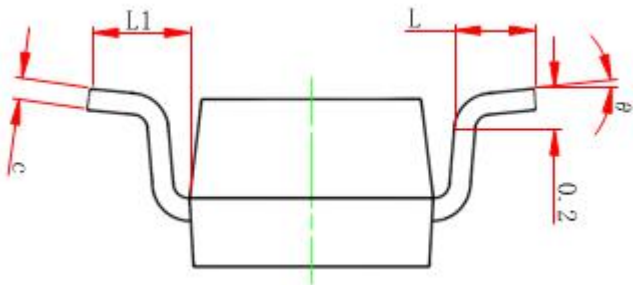
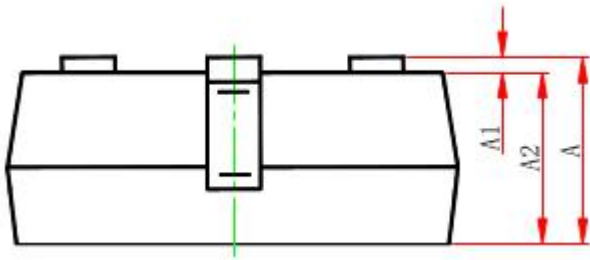
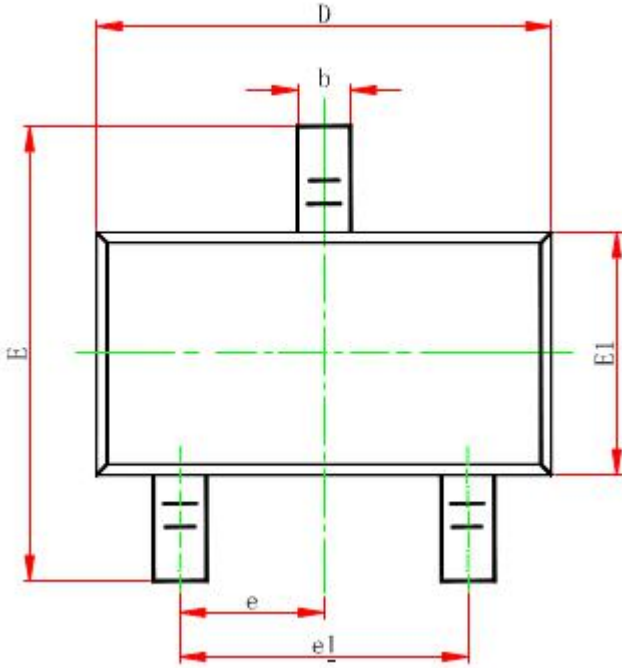
Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D =250uA, V _{GS} =0V)	BV _{DSS}	30	32	—	V
Gate Threshold Voltage 柵極開啓電壓(I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	1	—	3	V
Diode Forward Voltage Drop 內附二極管正向壓降(I _S = 1A, V _{GS} =0V)	V _{SD}	—	0.7	1	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V _{GS} =0V, V _{DS} = 30V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 柵極漏電流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I _D = 5A, V _{GS} =10V)	R _{DS(ON)}	—	24	28	mΩ
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I _D = 3A, V _{GS} =4.5V)	R _{DS(ON)}	—	38	45	mΩ
Input Capacitance 輸入電容 (V _{GS} =0V, V _{DS} = 15V, f=1MHz)	C _{ISS}	—	540	—	pF
Output Capacitance 輸出電容 (V _{GS} =0V, V _{DS} = 15V, f=1MHz)	C _{OSS}	—	60	—	pF
Turn-ON Time 開啓時間 (V _{DS} = 15V, V _{GS} = 10V, R _{GEN} =6Ω)	t _(on)	—	9.5	—	ns
Turn-OFF Time 關斷時間 (V _{DS} = 15V, V _{GS} = 10V, R _{GEN} =6Ω)	t _(off)	—	36	—	ns

Pulse Width≤300 μs; Duty Cycle≤2.0%

FS3404M

■ DIMENSION 外形封裝尺寸

單位(UNIT): mm



代码	范围(单位: mm)
A	1.050~1.250
A1	0.000~0.100
A2	1.050~1.150
b	0.300~0.500
c	0.100~0.200
D	2.820~3.020
E1	1.500~1.700
E	2.650~2.950
e	0.950(BSC)
e 1	1.800~2.00
L	0.300~0.600
L1	0.600REF.
θ	0°~8°